

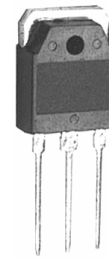


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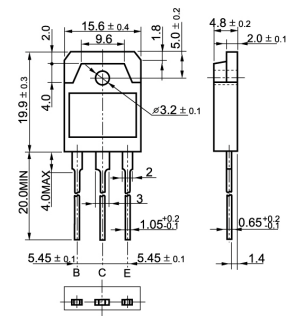
Silicon Epitaxial Planar Transistor

GENERAL DESCRIPTION

Silicon NPN high frequency, high power transistors in a plastic envelope, primarily for use in audio and general purpose



MT-100



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0V$	-	1100	V
V_{CEO}	Collector-emitter voltage (open base)		-	500	V
I_C	Collector current (DC)		-	12	A
I_{CM}	Collector current peak value		-		A
P_{tot}	Total power dissipation	$T_{mb} \leq 25^\circ C$	-	150	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 4.5A; I_B = 1.0A$	-	3	V
V_F	Diode forward voltage	$I_F = 4.5A$	1.5	2.0	V
t_f	Fall time	$I_C = 4.5A, I_{B1} = -I_{B2} = 0.8A, V_{CC} = 80V$	0.3	1.0-	μs

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0V$	-	1100	V
V_{CEO}	Collector-emitter voltage (open base)		-	500	V
V_{EBO}	Emitter-base voltage (open collector)			5	V
I_C	Collector current (DC)		-	12	A
I_B	Base current (DC)		-	3	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25^\circ C$	-	150	W
T_{sta}	Storage temperature		-55	150	$^\circ C$
T_j	Junction temperature		-	150	$^\circ C$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
I_{CBO}	Collector-base cut-off current	$V_{CB} = 1000V$	-	0.2	mA
I_{EBO}	Emitter-base cut-off current	$V_{EB} = 5V$	-	0.2	mA
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 1mA$	500		V
V_{CEsat}	Collector-emitter saturation voltages	$I_C = 4.5A; I_B = 1A$	-	3.0	V
h_{FE}	DC current gain	$I_C = 1.0A; V_{CE} = 5V$	10		
f_T	Transition frequency at $f = 5MHz$	$I_C = 1.0A; V_{CE} = 12V$	15	-	MHz
C_c	Collector capacitance at $f = 1MHz$	$V_{CB} = 10V$	280	-	pF
t_{on}	On times	$I_C = 4.5A, I_{B1} = -I_{B2} = 0.8A, V_{CC} = 80V$			us
t_s	Turn-off storage time	$I_C = 4.5A, I_{B1} = -I_{B2} = 0.8A, V_{CC} = 80V$			us
t_f	Fall time	$I_C = 4.5A, I_{B1} = -I_{B2} = 0.8A, V_{CC} = 80V$	0.3	1.0	us